Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	5280	438/592,682,527,530,597,301.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/01/27 09:40
L2	490	1 and (silicid$6 near3 anneal$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/01/27 09:42
L3	411	2 and implant$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/01/27 09:43
L4	31	3 and (transistor with (metal adj layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/01/27 09:46
L5	12	3 and (transistor with substrate with (metal adj layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/01/27 09:46
S1	769062	transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/26 10:51
S2	5900	transistor with (metal adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/26 10:53
S3	68	transistor with ((metal adj layer) with silicid$6 with anneal$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/26 10:57
S4	1281	((metal adj layer) with silicid$6 with anneal$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/26 10:58
S5	15	S4 and (remov$4 unsilicid$4 metal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/01/26 11:47

S6	11	S5 and (ion implant$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/01/26 11:46
S7	12	S5 and (ion near3 implant$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/01/26 11:47
S8	7	S4 and (remov$4 unsilicid$4 metal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2006/01/26 11:47
S9	5	S8 and (ion near3 implant$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/01/27 09:39